

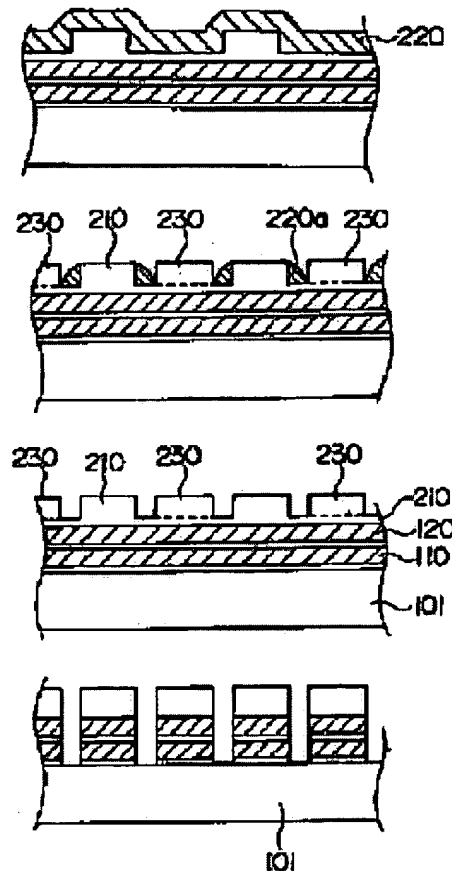
MANUFACTURE OF SEMICONDUCTOR DEVICE

Patent number: JP5190809
Publication date: 1993-07-30
Inventor: YAMADA YUZURU
Applicant: KAWASAKI STEEL CO
Classification:
- **international:** H01L27/115; H01L29/788; H01L29/792
- **europaen:**
Application number: JP19920004922 19920114
Priority number(s): JP19920004922 19920114

Report a data error here

Abstract of JP5190809

PURPOSE: To make it possible to achieve high integration density by suppressing the effects of the machining-size errors and the position deviation of a photo-mask. **CONSTITUTION:** A nitride film 220 is formed on an SiO₂ film 210. The nitride film 220 is removed by anisotropic plasma etching so that the sidewall part of the SiO₂ film 210 remains. The nitride film, which remains at the sidewall part of the SiO₂ film 210, becomes a spacer 220a. Then, an SiO₂ film 230 is formed. At this time, the spacer 220 acts as a mask for forming the SiO₂. The SiO₂ film 230 is formed at a part, where the spacer 220a is not present. The thick part of SiO₂ is used as an etching mask, and the etching is performed down to a polysilicon film 110. Thus a stack gate is formed.



Data supplied from the esp@cenet database - Worldwide